

L Number	Hits	Search Text	DB	Time stamp
176	15666	semiconductor and (band adj gap) and @ad<=20011012	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:13
177	10538	(semiconductor same (band adj gap)) and @ad<=20011012	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 10:51
178	8320	(semiconductor with (band adj gap)) and @ad<=20011012	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 10:51
179	1002	((semiconductor with (band adj gap)) and @ad<=20011012) and ((metal adj oxide adj semiconductor) or ("MOS"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:53
180	872	((semiconductor with (band adj gap)) and @ad<=20011012) and ((metal adj oxide adj semiconductor) or ("MOS")) and source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:53
181	680	((semiconductor with (band adj gap)) and @ad<=20011012) and ((metal adj oxide adj semiconductor) or ("MOS")) and source and within	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:54
182	265	((semiconductor with (band adj gap)) and @ad<=20011012) and ((metal adj oxide adj semiconductor) or ("MOS")) and (source same within)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:54
183	151	((semiconductor with (band adj gap)) and @ad<=20011012) and ((metal adj oxide adj semiconductor) or ("MOS")) and (source with within)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:14
184	843	(438/197).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:12
185	1706	(438/270).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:12
186	359	(438/271).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:13
187	1106	(257/288).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:13
188	694	(257/335).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:13
189	40	438/197,270,271.ccls. and (band adj gap) and @ad<=20011012	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 12:14

190	58	257/288,335,336,337,338,339,340,341,342,343.ccl and (band adj gap) and @ad<=20011012	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/03 12:14
191	6498	257/\$.ccls. and (band adj gap) and @ad<=20011012	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/03 12:15
192	2479	438/\$.ccls. and (band adj gap) and @ad<=20011012	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/03 12:15
193	1066	257/\$.ccls. and (band adj gap) and ((metal adj oxide adj semiconductor) or ("MOS")) and source and within and @ad<=20011012	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/03 12:15
194	425	438/\$.ccls. and (band adj gap) and ((metal adj oxide adj semiconductor) or ("MOS")) and source and within and @ad<=20011012	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/03 12:16
196	198	438/\$.ccls. and (band adj gap) and ((metal adj oxide adj semiconductor) or ("MOS")) and (source same within) and @ad<=20011012	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/03 12:16
197	487	257/\$.ccls. and (band adj gap) and ((metal adj oxide adj semiconductor) or ("MOS")) and (source same within) and @ad<=20011012	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/03 12:16
195	128	438/\$.ccls. and (band adj gap) and ((metal adj oxide adj semiconductor) or ("MOS")) and (source with within) and @ad<=20011012	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/03 12:17
198	300	257/\$.ccls. and (band adj gap) and ((metal adj oxide adj semiconductor) or ("MOS")) and (source with within) and @ad<=20011012	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/03 12:26